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					Applicant(s) Jagannathan et al.					
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L. D. Lanzerotti et al., "Suppression of Boron Outdiffusion in SiGe HBTs by Carbon Incorporation", 1996 IE 96-249, pp. 10.2.1-10.2.4										
MLT										
MLT		films" J. Appl. Phys. 71 (10), 15 May 1992 p. 4820-4825 J. W. Matthews et al., " Defects in Epitaxial Multilayers", Journal of Crystal Growth 27 (1974), pp. 118-125								
EXAMINER Minhloan Train				D	ATE CONSIDERED	5/2	2003			
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